

# 20A, 100V - 120V Low V<sub>F</sub> Schottky Barrier Rectifier

#### **FEATURES**

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

#### **APPLICATIONS**

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

### **MECHANICAL DATA**

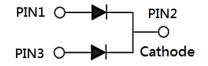
- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.90g (approximately)

KEY PARAMETERS		
PARAMETER	VALUE	UNIT
I <sub>F</sub>	20	А
V <sub>RRM</sub>	100 - 120	V
I <sub>FSM</sub>	150	А
T <sub>J MAX</sub>	150	°C
Package	TO-220AB	
Configuration	Dual d	lies





TO-220AB



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C un	less otherwise r	noted)		
PARAMETER	SYMBOL	MBR20L100CT	MBR20L120CT	UNIT
Marking code on the device		MBR20L100CT	MBR20L120CT	
Repetitive peak reverse voltage	V <sub>RRM</sub>	100	120	V
Reverse voltage, total rms value	V <sub>R(RMS)</sub>	70	84	V
Forward current	I <sub>F</sub>	20		А
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>	150		А
Peak repetitive reverse surge current <sup>(1)</sup>	I <sub>RRM</sub>	1		А
Peak repetitive forward current (Rated $V_{R}$ , Square wave, 20KHz)	I <sub>FRM</sub>	20		А
Critical rate of rise of off-state voltage	dv/dt	10,000		V/µs
Junction temperature	TJ	-55 to +150		°C
Storage temperature	T <sub>STG</sub>	-55 to +150		°C

- Notes:
- 1. tp = 2.0µs, 1.0KHz



THERMAL PERFORMANCE				
PARAMETER		SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	MBR20L100CT	$R_{\Theta JC}$	2.8	°C/W
Junction-to-case thermal resistance	MBR20L120CT	$R_{\Theta JC}$	3.0	°C/W

ELECTRICAL SPECIF	ICATIONS (T	A = 25°C unless otherv	vise noted)				
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT	
	MBR20L100CT	$I_F = 10A, T_J = 25^{\circ}C$	V <sub>F</sub>	0.72	0.75	V	
	MBR20L120CT			0.78	0.83	V	
	MBR20L100CT	$I_F = 20A, T_J = 25^{\circ}C$		0.81	0.85	V	
Forward voltage per diode <sup>(1)</sup>	MBR20L120CT			0.86	0.90	V	
	MBR20L100CT	$I_F = 10A, T_J = 125^{\circ}C$		0.58	0.68	V	
	MBR20L120CT			0.63	0.72	V	
	MBR20L100CT	$I_F = 20A, T_J = 125^{\circ}C$		0.67	0.75	V	
	MBR20L120CT			0.73	0.80	V	
Reverse current @ rated $V_R$ per diode <sup>(2)</sup>	Reverse current @ rated $V_{R}$	MBR20L100CT MBR20L120CT	$T_J = 25^{\circ}C$	-	-	20	μA
	MBR20L100CT	T <sub>J</sub> = 125°C	I <sub>R</sub>	-	15	mA	
	MBR20L120CT			-	10	mA	

#### Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING
MBR20LxCT	TO-220AB	50 / Tube
MBR20LxCTH	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 100V(MBR20L100CT) to 120V(MBR20L120CT)

2. "H" means AEC-Q101 qualified



## MBR20L100CT – MBR20L120CT

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#### **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

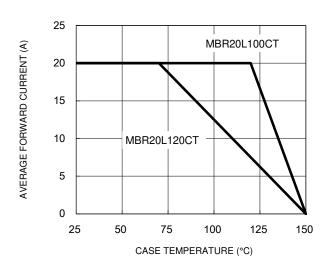
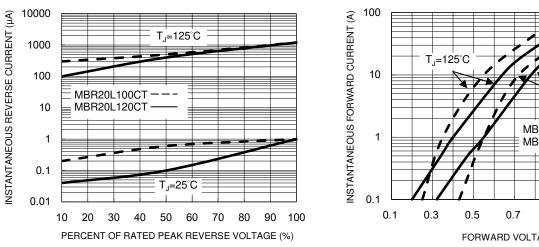
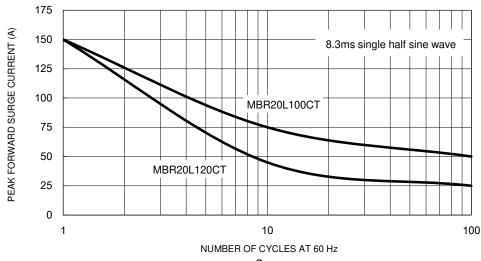


Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**



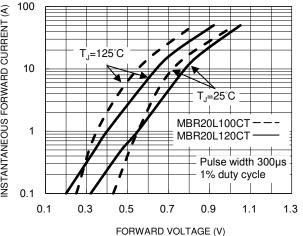
#### Fig.5 Maximum Non-Repetitive Forward Surge Current



10000 CAPACITANCE (pF) 1000 MBR20L100CT MBR20L120CT 100 f=1.0MHz Vsig=50mVp-p 10 10 100 0.1 1

#### **REVERSE VOLTAGE (V)**

#### **Fig.4 Typical Forward Characteristics**

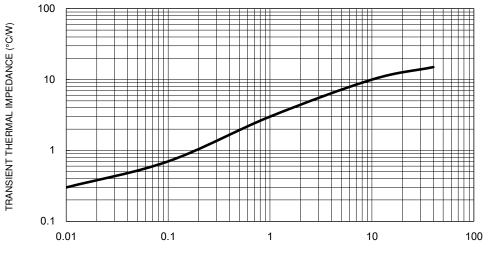


**Fig.2 Typical Junction Capacitance** 



## **CHARACTERISTICS CURVES**

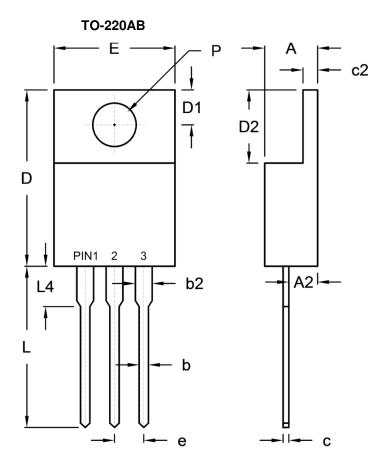
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



#### Fig.6 Typical Transient Thermal Impedance

PULSE DURATION (s)

## PACKAGE OUTLINE DIMENSIONS



DIM.	Unit (mm)		Unit (	(inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
b2	1.14	1.77	0.045	0.070
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
L	13.19	14.79	0.519	0.582
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

### **MARKING DIAGRAM**



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



# MBR20L100CT – MBR20L120CT

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